Silicon PNP Power Transistors 2SA1880

DESCRIPTION

- With ITO-220 package
- Switching power transistor
- Low collector saturation voltage

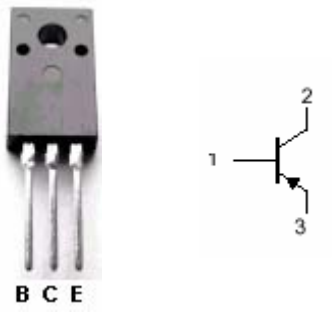


Fig.1 simplified outline (ITO-220) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-10	A
I_{CM}	Collector current-Peak		-20	A
I_B	Base current		-1.5	A
I_{BM}	Base current-Peak		-2	A
P_T	Total power dissipation	T_C=25℃	25	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction case	5.0	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=-0.1A ;I_B=0	-80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A; I_B=-0.5A			-0.3	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-5A; I_B=-0.5A			-1.2	V
I_{CBO}	Collector cut-off current	At rated volatge			-0.1	mA
I_{CEO}						
I_{EBO}	Emitter cut-off current	At rated volatge			-0.1	mA
h_{FE}	DC current gain	I_C=-5A ; V_{CE}=-2V	70			
f_T	Transition frequency	I_C=-1A ; V_{CE}=-10V		50		MHz

Switching times

t_{on}	Turn-on time	I_C=-5A;I_{B1}=-I_{B2}=-0.5A , R_L=5Ω ;V_{BB2}=-4V			0.3	μs
t_s	Storage time				1.5	μs
t_f	Fall time				0.2	μs

PACKAGE OUTLINE

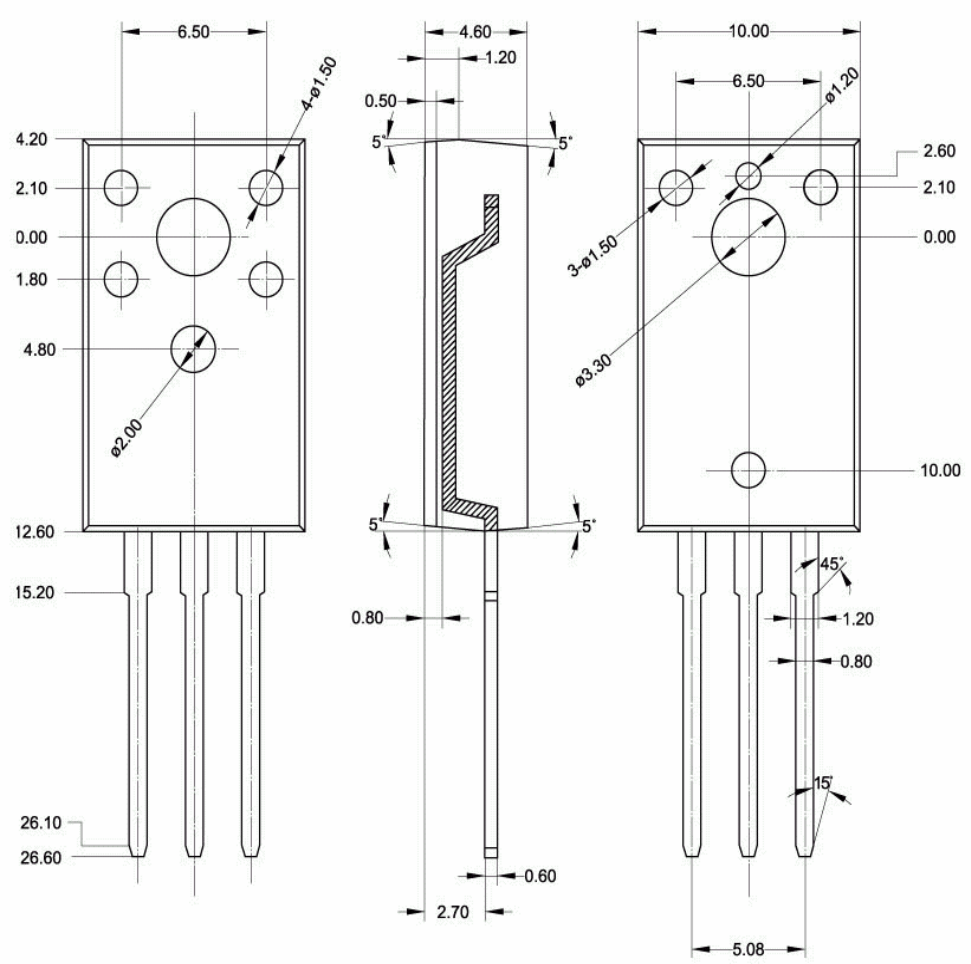


Fig.2 Outline dimensions (unindicated tolerance:±0.20 mm)